

# **HD74LS165A**

## Parallel-Load 8-bit Shift Register

REJ03D0449-0300 Rev.3.00 Jul.15.2005

The LS165A are 8-bit serial shift registers that shift the data in the direction of  $Q_A$  toward  $Q_H$  when clocked. Parallel-in access to each stage is made available by eight individual direct data inputs that are enabled by a low level at the shift / load input. These registers also feature gated clock inputs and complementary outputs from the eighth bit. All inputs are diode-clamped to minimize transmission-line effects, thereby simplifying system design.

Clocking is accomplished through a 2-input positive-NOR gate, permitting one input to be used as a clock-inhibit function. Holding either of the clock inputs high inhibits clocking and holding either clock input low with the shift / load input high enables the other clock input. The clock-inhibit input should be changed to the high level only while the clock input is high. Parallel loading is inhibited as long as the shift / load input is high. Data at the parallel inputs are loaded directly into the register on a high-to-low transition of the shift / load input independently of the levels of the clock, clock inhibit, or serial inputs.

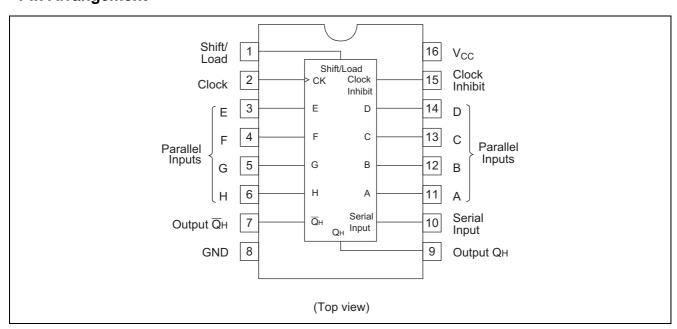
#### **Features**

### • Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LS165AP	DILP-16 pin	PRDP0016AE-B (DP-16FV)	Р	_
HD74LS165AFPEL	SOP-16 pin (JEITA)	PRSP0016DH-B (FP-16DAV)	FP	EL (2,000 pcs/reel)

Note: Please consult the sales office for the above package availability.

### **Pin Arrangement**



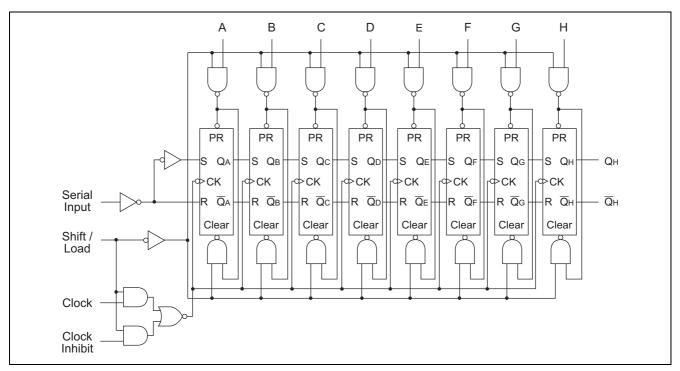
### **Function Table**

		Inputs	Internal outputs		Outmut.		
Shift / Load	Clock	Clock	ck Serial Parallel		Internal	Output Q <sub>H</sub>	
Silit / Loau	Inhibit	Clock	AH	Q <sub>A</sub>	Q <sub>B</sub>	] <b>Ч</b> н	
L	Х	X	Х	ah	а	b	h
Н	L	1	Х	Х	$Q_{A0}$	Q <sub>B0</sub>	Q <sub>H0</sub>
Н	L	1	Н	Х	Н	Q <sub>An</sub>	$Q_{Gn}$
Н	L	1	L	Х	L	Q <sub>An</sub>	$Q_{Gn}$
Н	Н	Х	Х	Х	Q <sub>A0</sub>	Q <sub>B0</sub>	Q <sub>H0</sub>

Notes: 1. H; high level, L; low level, X; irrelevant

- 2. 1; transition from low to high level
- 3. a to h; the level of steady-state input at inputs A to H respectively
- 4. Q<sub>A0</sub> to Q<sub>H0</sub>; the level of Q<sub>A</sub> to Q<sub>H</sub>, respectively, before the indicated steady-state input conditions were established.
- 5.  $Q_{An}$  to  $Q_{Gn}$ ; the level of  $Q_A$  to  $Q_G$ , respectively, before the most recent  $\downarrow$  transition of the clock.

## **Block Diagram**



## **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit
Supply voltage	V <sub>CC</sub>	7	V
Input voltage	V <sub>IN</sub>	7	V
Power dissipation	P <sub>T</sub>	400	mW
Storage temperature	Tstg	-65 to +150	°C

Note: Voltage value, unless otherwise noted, are with respect to network ground terminal.

## **Recommended Operating Conditions**

Item	Symbol	Min	Тур	Max	Unit
Supply voltage	V <sub>CC</sub>	4.75	5.00	5.25	V
Output current	Іон	_	_	-400	μΑ
Output current	I <sub>OL</sub>	_	_	8	mA
Operating temperature	T <sub>opr</sub>	-20	25	75	°C
Clock frequency	$f_{\sf clock}$	0	_	25	MHz
Clock pulse width	t <sub>w (clock)</sub>	25	_	_	ns
Load pulse width	t <sub>w (load)</sub>	15	_	_	ns
Clock enable setup time	t <sub>su</sub>	30	_	_	ns
Parallel input setup time	t <sub>su</sub>	10	_	_	ns
Serial input setup time	t <sub>su</sub>	20	_	_	ns
Shift setup time	t <sub>su</sub>	45	_	_	ns
Hold time	t <sub>h</sub>	0	_	_	ns

## **Electrical Characteristics**

 $(Ta = -20 \text{ to } +75 \text{ }^{\circ}\text{C})$ 

Item		Symbol	min.	typ.*	max.	Unit	Condition	
Input voltage		$V_{IH}$	2.0	_	_	V		
Input voltage		$V_{IL}$	_	_	0.8	V		
		V <sub>OH</sub>	2.7		_	>	$V_{CC} = 4.75 \; V,  V_{IH} = 2 \; V,  V_{IL} = 0.8 \; V, \\ I_{OH} = -400 \; \mu A$	
Output voltage		V <sub>a</sub> .			0.4	V	$I_{OL} = 4 \text{ mA}$ $V_{CC} = 4.75 \text{ V}, V_{IH} = 2 \text{ V},$	
		$V_{OL}$			0.5	٧	$I_{OL} = 8 \text{ mA}$ $V_{IL} = 0.8 \text{ V}$	
Input ourront	Shift / Load	1.		_	0.3	mA	V <sub>CC</sub> = 5.25 V, V <sub>I</sub> = 7 V	
Input current	Other inputs	l <sub>l</sub>	_	_	0.1	mA	VCC = 5.25 V, V  = 1 V	
High level	Shift / Load	L	_	_	60	μΑ	V <sub>CC</sub> = 5.25 V, V <sub>I</sub> = 2.7 V	
input current	Other inputs	I <sub>IH</sub>	_	_	20	μΑ	VCC = 5.25 V, V  = 2.7 V	
Low level input	Shift / Load		_	_	-1.2	mA	V <sub>CC</sub> = 5.25 V, V <sub>I</sub> = 0.4 V	
current Other inputs		I₁∟	_	_	-0.4	mA	VCC = 5.25 V, VI = 0.4 V	
Short-circuit output current		Ios	-20	_	-100	mA	V <sub>CC</sub> = 5.25 V	
Supply current**		Icc	_	21	36	mA	V <sub>CC</sub> = 5.25 V	
Input clamp voltage		V <sub>IK</sub>	_	_	-1.5	V	$V_{CC} = 4.75 \text{ V}, I_{IN} = -18 \text{ mA}$	

Note:  $V_{CC} = 5 \text{ V}, \text{ Ta} = 25^{\circ}\text{C}$ 

## **Switching Characteristics**

 $(V_{CC} = 5 \text{ V}, \text{ Ta} = 25^{\circ}\text{C})$ 

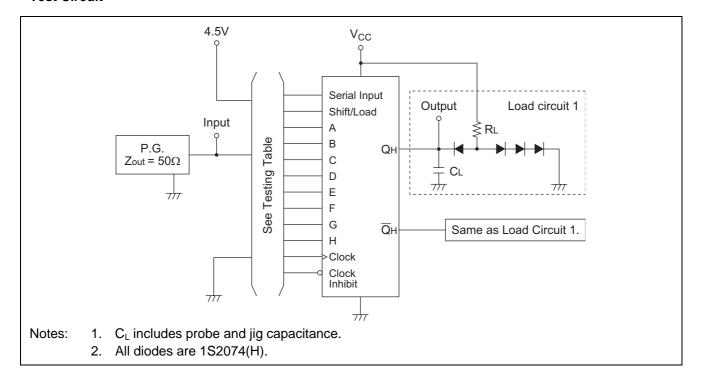
Item	Symbol	Inputs	Outputs	min.	typ.	max.	Unit	Condition
Maximum clock frequency	$f_{\sf max}$			25	35	_	MHz	
	$t_{PLH}$	Load	Anu		21	35	ns	$C_L = 15 \text{ pF},$ $R_L = 2 \text{ k}\Omega$
	$t_{PHL}$	Luau	Any		26	35	ns	
Draw a gratic podelov time	$t_{PLH}$	Clock	Any		14	25	ns	
	$t_{PHL}$				16	25	ns	
Propagation delay time	t <sub>PLH</sub>	Н	Q <sub>H</sub>	1	13	25	ns	
	t <sub>PHL</sub>			1	24	30	ns	
	t <sub>PLH</sub>	Н	Q <sub>H</sub>		19	30	ns	
	t <sub>PHL</sub>	11			17	25	ns	

RENESAS

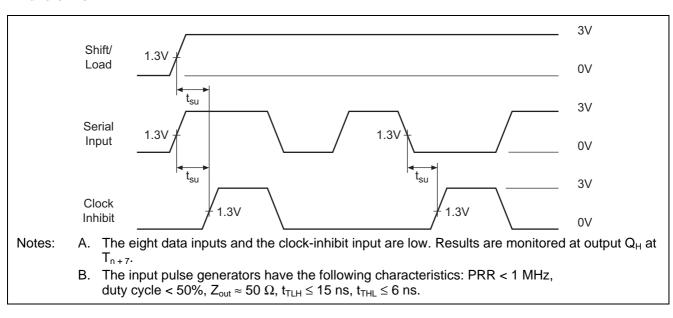
<sup>\*\*.</sup> With the outputs open, clock inhibit and clock at 4.5 V, and a clock pulse applied to the shift / load,  $I_{CC}$  is measured with the parallel inputs at 4.5 V, than with the parallel inputs grounded.

## **Testing Method**

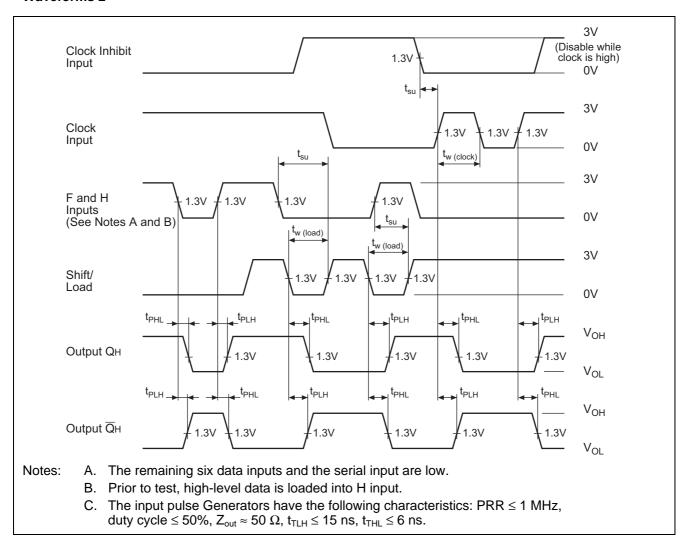
### **Test Circuit**



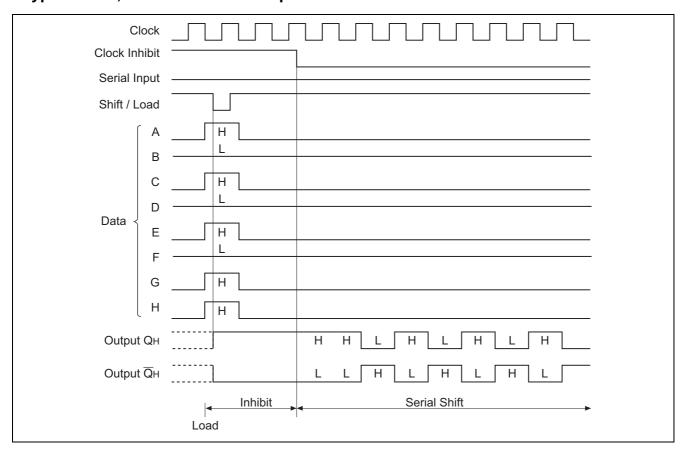
### Waveforms 1



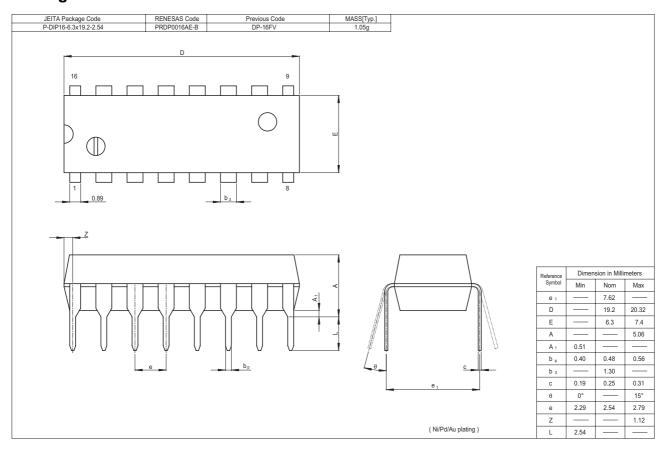
#### Waveforms 2

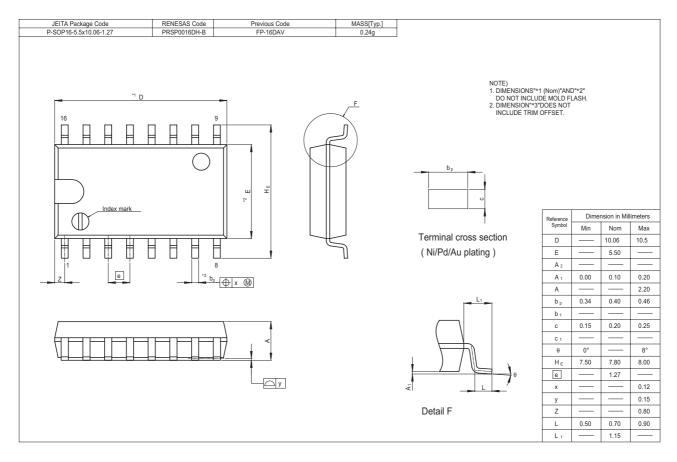


## Typical Shift, Load and Inhibit Sequences



## **Package Dimensions**





Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs!

1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal righty, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

#### Notes regarding these materials

- Notes regarding these materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.

  2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.

  3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein.

  The information described here may contain technical inaccuracies or typographical errors.

  Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.

  Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (http://www.renesas.com).
- home page (http://www.renesas.com).

  4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.

  5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.

  6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials.

  7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.

  Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.

  8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.



#### **RENESAS SALES OFFICES**

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information

**Renesas Technology America, Inc.** 450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd. Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

**Renesas Technology Korea Co., Ltd.**Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

0	2005	Panasas Tachnology Corn	All rights reserved	Printed in Ianan